

SAN JOSE STATE UNIVERSITY
Electrical Engineering Department

EE288 Data Conversions/Analog Mixed-Signal ICs

Spring 2018

Midterm Exam

Instructor: Sang-Soo Lee

Problem	Score	Max Score
1		5
2		5
3		5
4		5
5		5
6		5
Total		30

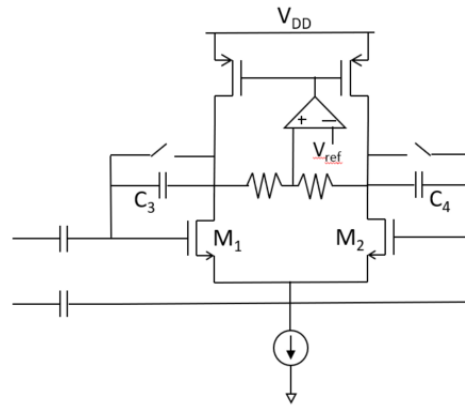
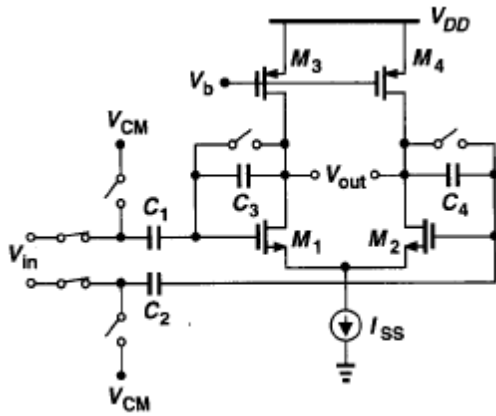
Name: _____

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Problem 1 (5 points)

Consider the switched-capacitor circuit below, where the CMFB is not shown. Assume $(W/L)_{1-4} = 50/0.5$. $I_{ss} = 1\text{mA}$, $C_1 = C_2 = 2\text{pF}$, $C_3 = C_4 = 0.5\text{pF}$, and the output common-mode level is 1.5V . Neglect the transistor capacitances. Assume $\lambda = 0.1\text{ V}^{-1}$ and $V_{dsat} = 0.2\text{V}$ for all transistors.

- Draw a common-mode feedback circuit that can work with the main amplifier on the right side of the circuit and explain the operation of the CMFB loop.
- Calculate the open loop gain of the amplifier.
- Calculate the gain error of the closed-loop SC amplifier.

Open loop gain

$$\begin{aligned}
 A &= g_{m1} r_{out} \\
 &= g_{m1} (r_{o1} // r_{o3}) \\
 &= (2I / V_{dsat}) [1 / (\lambda_n I + \lambda_p I)] \\
 &= (2 / V_{dsat}) [1 / (\lambda_n + \lambda_p)] \\
 &= (2 / 0.2) (1 / 0.2) = 50
 \end{aligned}$$

Gain error of the switched-capacitor circuit is $1/\beta A$

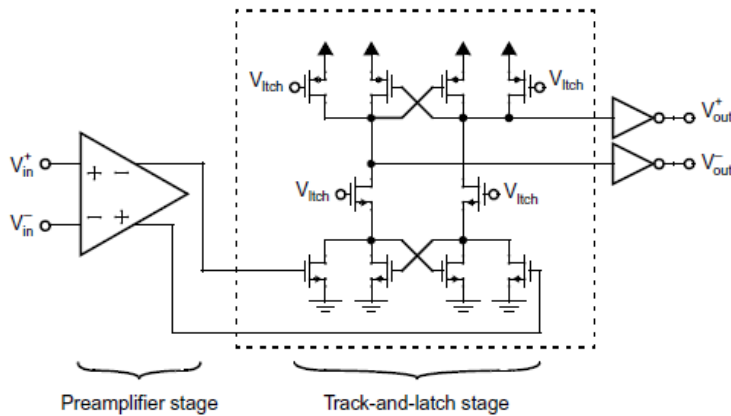
$$\begin{aligned}
 \beta &= C_3 / (C_1 + C_3) \\
 &= 0.5 / (2 + 0.5) \\
 &= 1/5
 \end{aligned}$$

$$1/\beta A = 5/50 = 0.1$$

Problem 2 (5 points)

The following latched comparator has been designed for a 10-bit ADC running at 100MHz sampling rate. The preamp has a differential pair with $W/L = 2(1.6\mu\text{m}/0.2\mu\text{m})$. Assume there is 10mV latch offset and the offset of the preamp is dominated by the differential pair mismatch.

- Calculate the offset of the preamp using Pelgrom's model. Assume $A_{vt} = 2.4\text{mV} \cdot \mu\text{m}$.
- Determine the gain of the preamp to achieve 5mV overall input referred offset.
- Suggest a preamplifier circuit to achieve the gain you calculated in (b). Clearly show the size for the appropriate transistors in the suggested circuit. Assume $\mu_n = 200\mu\text{A}/\text{V}^2$ and $\mu_p = 100\mu\text{A}/\text{V}^2$.
- What is the gain you can achieve with the regenerative latch if V_{latch} is high during 80% of the half clock period for the latch regeneration? Assume the latch regeneration time constant is 0.5ns.



Offset of the preamp caused by the differential pair mismatch

$$\begin{aligned}
 V_{os} &= A_{vt} / \sqrt{WL} \\
 &= 2.4\text{mV} / \sqrt{2 \times 1.6 \times 0.2} \\
 &= 2.4\text{mV} / 0.8 \\
 &= 3\text{mV}
 \end{aligned}$$

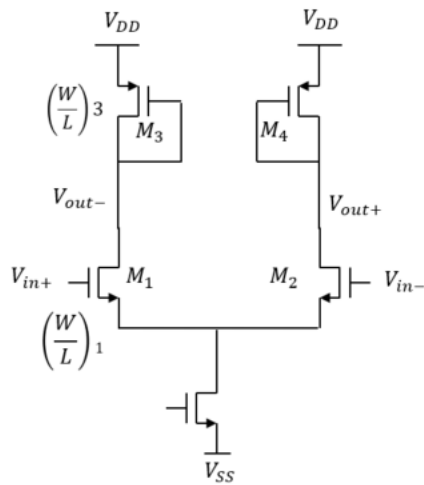
Overall input referred offset

$$\begin{aligned}
 V_{os}^2 &= V_{os_preamp}^2 + (V_{os_latch}/A)^2 \\
 5\text{mV}^2 &= 3\text{mV}^2 + (10\text{mV}/A)^2 \\
 A &= 2.5
 \end{aligned}$$

Gain of the regenerative latch

$$\begin{aligned}
 80\% \text{ of the half clock} &= 0.8 \times 5\text{ns} = 4\text{ns} \\
 \text{Time constant } \tau &= 0.5\text{ns} \\
 \text{Gain} &= \exp(t/\tau) = \exp(4\text{ns}/0.5\text{ns}) = \exp(8) = 2981
 \end{aligned}$$

Preamplifier circuit and the size calculation



$$Gain = \frac{\sqrt{2\mu_n C_{ox} \frac{W}{L} M_1 I_{D1}}}{\sqrt{2\mu_p C_{ox} \frac{W}{L} M_3 I_{D3}}} = \frac{\sqrt{200 \frac{W}{L} M_1}}{\sqrt{100 \frac{W}{L} M_3}} = \sqrt{\frac{2 \frac{W}{L} M_1}{\frac{W}{L} M_3}} = 2.5$$

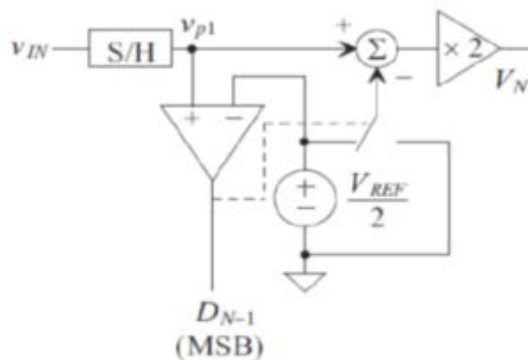
$$2 \frac{W}{L} M_1 = \frac{W}{L} M_3 (2.5)^2$$

$$\frac{W}{L} M_1 = 3.125 \frac{W}{L} M_3$$

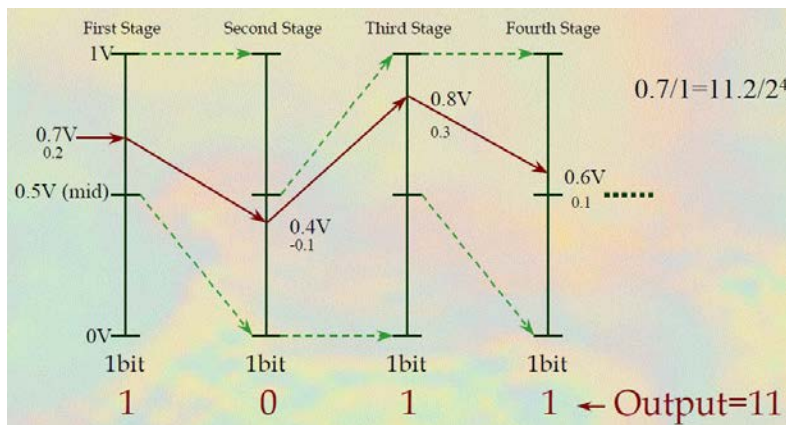
Problem 3 (5 points)

You are building a 4-bit pipelined ADC based on 1-bit per stage architecture. Assume the Full-scale input signal range is 0 ~ 1V, and Vrefp=1V and Vrefm=0V.

- (a) Sketch the 1-bit/stage circuit using ideal components and describe how the pipeline stage works.



- (b) Assume an input signal of 0.7V. Provide analog and digital output values for each and every stage for the 4-bit ADC. Analog values should be between 0V and 1V, and the digital values should be either 0 or 1.



Problem 4 (5 points)

Spectral testing has been performed on a 12-bit ADC by using a 3MHz full-scale sinusoidal input, sampling frequency of 10MHz, and 1024-point FFT. Use below spectral plot to answer the followings.

- Draw the input signal tone on the spectral plot below assuming no windowing required.
- Compute the ideal SQNR for this ADC.
- By raising the chip temperature and re-measuring the SNR, the effect of thermal noise is estimated as 5dB extra SNR degradation at the ambient temperature. Find the overall SNR at the ambient temperature.
- Using the SNR result found in c), find the value for the noise floor level shown as Y[dB] on the spectral test graph.
- Due to sampling without an antialiasing filter, aliased second and third harmonics showed up in the plot. Assuming the aliased second harmonic is -79dBFS and the third harmonic is -72dBFS, plot the aliased tones in the graph.

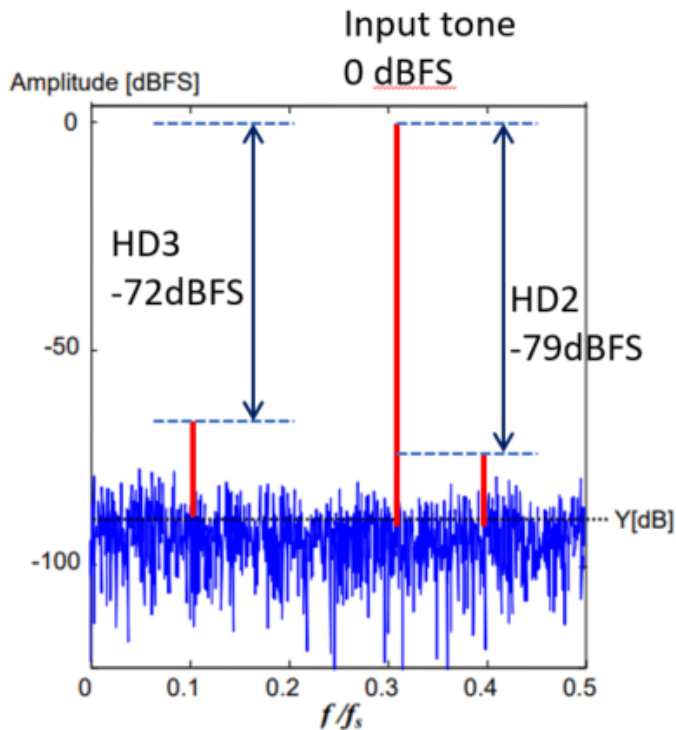
$$\text{Input freq} = 3\text{MHz}, \text{Sampling freq} = 10\text{MHz} \rightarrow f_{\text{in}}/f_s = 3/10 = 0.3$$

$$\text{SQNR} = 6.02 N + 1.76 = 6.02 \times 12 + 1.76 = 74 \text{ dB}$$

$$\text{SNR} = 74 - 5 = 69 \text{ dB}$$

Noise floor

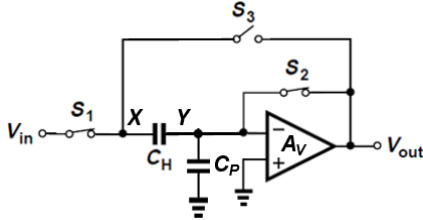
$$Y[\text{dB}] = -69 - 10 \log [2^N/2] = -69 - 10 \log(1024/2) = -69 - 27 = -96 \text{ dB}$$



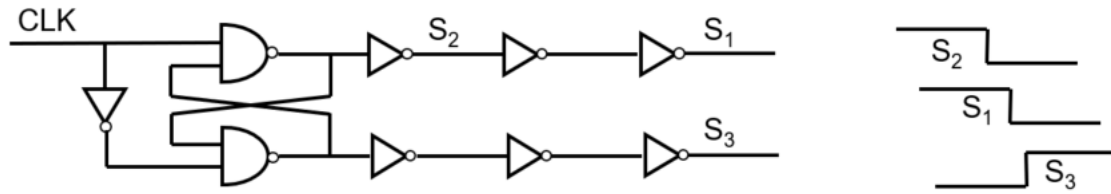
Problem 5 (5 points)

For the flip-around S/H circuit shown below,

- Explain where the bottom plate of the capacitor C_H should be connected to. X or Y?
- Provide a clock generation circuit to control the switches S_1 , S_2 , and S_3 based on bottom plate sampling scheme.
- What is the feedback factor during the hold mode?
- Derive the closed-loop gain expression (V_{out}/V_{in}) using the charge conservation method.



Bottom plate usually has higher parasitic capacitance. Therefore, we should connect the bottom plate to X to reduce the summing node capacitance. This will increase the feedback factor of the Switched-Capacitor circuit.



$$\beta = C_H / (C_H + C_P)$$

Charge conservation during ϕ_1 and ϕ_2

During ϕ_1 , total charge at summing node is $Q_1 = C_H(0 - V_{in})$

During ϕ_2 , total charge at summing node is $Q_2 = C_p V_Y + C_H(V_Y - V_{out})$

Let $Q_1 = Q_2$

$$-V_{in}C_H = C_p V_Y + C_H(V_Y - V_{out}) = (C_p + C_H)V_Y - C_H V_{out}$$

$$V_Y (-A_{v1}) = V_{out}$$

$$-V_{in}C_H = (C_p + C_H) (-V_{out}/A_{v1}) - C_H V_{out}$$

$$V_{in}C_H = (C_p + C_H) (V_{out}/A_{v1}) + C_H V_{out}$$

$$V_{in}C_H = [(C_p + C_H) / A_{v1} + C_H] V_{out}$$

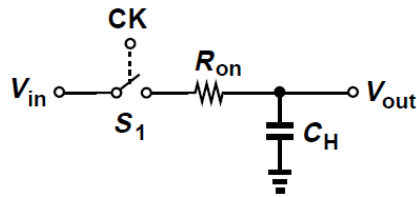
$$V_{in} = [(C_p + C_H) / (C_H A_{v1}) + 1] V_{out}$$

$$V_{out}/V_{in} = 1 / [(C_p + C_H) / (C_H A_{v1}) + 1] = 1 / [1 + 1/(\beta A_{v1})]$$

Problem 6 (5 points)

Consider the following sampling circuit with an ideal switch S_1 , where $R_{on}=400\ \Omega$. The circuit has been designed for a 10-bit system with Full Scale = 1V.

- How large should we choose the value of the sampling capacitance C_H so that the rms noise from the sampler is equal to 0.25LSB of the ADC at $T = 27^\circ\text{C}$? $K=1.38 \times 10^{-23}$.
- Compared to the case where only quantization noise is present, how much is the overall SNR degraded by the kT/C noise?
- If the clock CK has a 50% duty cycle, calculate the maximum clock frequency at which inputs between 0~1V can be sampled to within 1/2 LSB accuracy at 10-bit resolution? Assume the sampling capacitance $C_H = 1\text{pF}$.
- The switch has been implemented with an NMOS. What are the other factors affecting the accuracy of this sampling circuit?



(a) rms noise variance is KT/C

$$1\text{ LSB} = V_{FS}/2^N = 1/2^{10} = 1/1024 = \Delta$$

$$\text{sqrt}(KT/C) = \Delta / 4 = 1 / (4 \times 1024)$$

$$C = KT / (1/ (4 \times 1024))^2 = 1.38 \times 10^{-23} \times 300 \times 16 \times 1024^2 = 69.5\text{ fF}$$

(b) Original SNR = $10 \log (\text{Signal Power} / \text{Quantization Noise})$

$$\text{New SNR} = 10 \log [\text{Signal Power} / (\text{Quantization Noise} + KT/C)]$$

Original SNR – New SNR

$$= 10 \log (\text{Quantization Noise} + KT/C) / \text{Quantization Noise})$$

$$= 10 \log [(\Delta^2/12 + (\Delta/4)^2) / (\Delta^2/12)]$$

$$= 10 \log [(1/12 + 1/16) / (1/12)]$$

$$= 10 \log (1 + 12/16)$$

$$= 2.43\text{ dB}$$

$$(c) \text{Error} = V_{FS} \exp(-t/ \tau) = \Delta/2 = (V_{FS} /2^N)/2 \rightarrow t = \tau \ln (2^{N+1})$$

$$\tau = RC = 400\Omega \times 1\text{pF} = 4 \times 10^{-10}$$

$$t = \tau \ln (2^{11}) = 7.62 \tau = T_{\max} / 2 = 1/(2 \times f_{\max})$$

$$f_{\max} = 1/(2 \times 7.62 \times 4 \times 10^{-10}) = 164\text{ MHz}$$

(d) NMOS sampling circuit will have signal dependent nonlinearity, charge injection and clock feedthrough error.